30 September 2025

**Product data sheet** 

## 1. General description

PNP/PNP low  $V_{CEsat}$  transistor in a leadless medium power DFN2020-6 (SOT1118) Surface-Mounted Device (SMD) plastic package.

NPN/PNP complement: PBSS4130PANP NPN/NPN complement: PBSS4130PAN

### 2. Features and benefits

- Very low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain h<sub>FE</sub> at high I<sub>C</sub>
- · Reduced Printed-Circuit Board (PCB) requirements
- High energy efficiency due to less heat generation

## 3. Applications

- Load switch
- · Battery-driven devices
- · Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-2	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -0.1 A; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	250	mΩ



30 V, 1 A PNP/PNP low VCEsat transistor

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		
2	B1	base TR1	6 5 4	C1 B2 E2
3	C2	collector TR2		
4	E2	emitter TR2		(TR1) TR2)
5	B2	base TR2		
6	C1	collector TR1	1 2 3	E1 B1 C2
7	C1	collector TR1	Transparent top view  DFN2020-6 (SOT1118)	sym138
8	C2	collector TR2	DF142020-6 (3011116)	

# 6. Ordering information

### **Table 3. Ordering information**

Type number Package				
	Name	Description	Version	
PBSS5130PAP	DFN2020-6	plastic, leadless thermal enhanced ultra thin small outline package; no leads; 6 terminals; 0.65 mm pitch; 2 mm x 2 mm x 0.65 mm body	SOT1118	

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PBSS5130PAP	2E

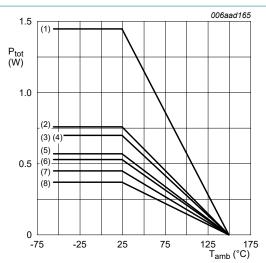
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or		'	<u> </u>		
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
$V_{CEO}$	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-1	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	А
I <sub>B</sub>	base current			-	-0.3	А
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	370	mW
			[2]	-	570	mW
			[3]	-	530	mW
			[4]	-	700	mW
			[5]	-	450	mW
			[6]	-	760	mW
			[7]	-	700	mW
			[8]	-	1450	mW
Per device				'		
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	510	mW
			[2]	-	780	mW
			[3]	-	730	mW
			[4]	-	960	mW
			[5]	-	620	mW
			[6]	-	1040	mW
			[7]	-	960	mW
			[8]	-	2000	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.



- (1) 4-layer PCB 70  $\mu m,$  mounting pad for collector 1  $\mbox{cm}^2$
- (2) FR4 PCB 70 μm, mounting pad for collector 1 cm<sup>2</sup>
- (3) 4-layer PCB 70 µm, standard footprint
- (4) 4-layer PCB 35 μm, mounting pad for collector 1 cm<sup>2</sup>
- (5) FR4 PCB 35 μm, mounting pad for collector 1 cm<sup>2</sup>
- (6) 4-layer PCB 35 µm, standard footprint
- (7) FR4 PCB 70 µm, standard footprint
- (8) FR4 PCB 35 µm, standard footprint

Fig. 1. Per transistor: power derating curves

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor						
R <sub>th(j-a)</sub>		n to ambient	[1]	-	-	338	K/W
	junction to ambient		[2]	-	-	219	K/W
			[3]	-	-	236	K/W
			[4]	-	-	179	K/W
			[5]	-	-	278	K/W
			[6]	-	-	164	K/W
			[7]	-	-	179	K/W
			[8]	-	-	86	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	30	K/W
Per device							
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	245	K/W
	junction to ambient	junction to ambient	[2]	-	-	160	K/W
			[3]	-	-	171	K/W
			[4]	-	-	130	K/W
			[5]	-	-	202	K/W
			[6]	-	-	120	K/W
			[7]	-	-	130	K/W
			[8]	-	-	63	K/W

- [1] Device mounted on an FR4 PCB, single-sided 35 µm copper strip line, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided 35 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated and standard footprint.
- [4] Device mounted on 4-layer PCB 35 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [5] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated and standard footprint.
- [6] Device mounted on an FR4 PCB, single-sided 70 µm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- [7] Device mounted on 4-layer PCB 70 µm copper strip line, tin-plated and standard footprint.
- [8] Device mounted on 4-layer PCB 70 μm copper strip line, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

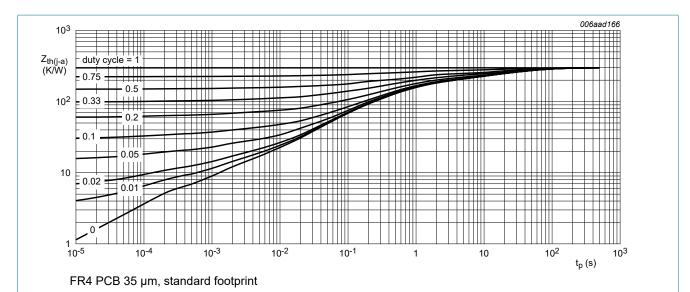


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

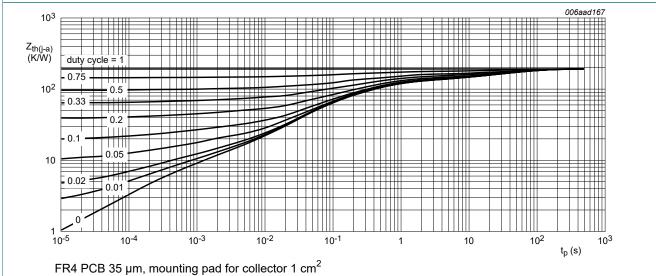


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

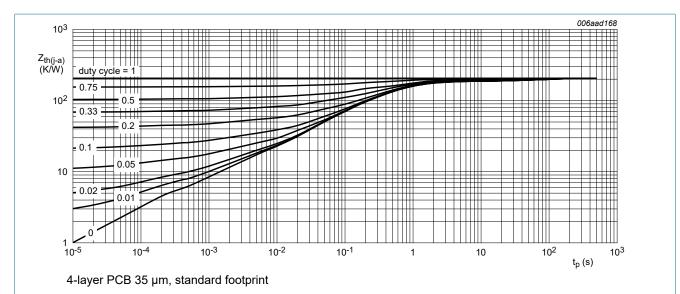


Fig. 4. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

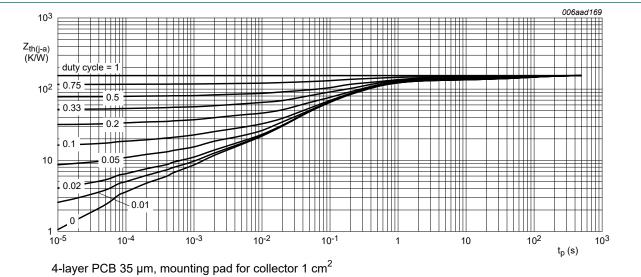


Fig. 5. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 30 V, 1 A PNP/PNP low VCEsat transistor

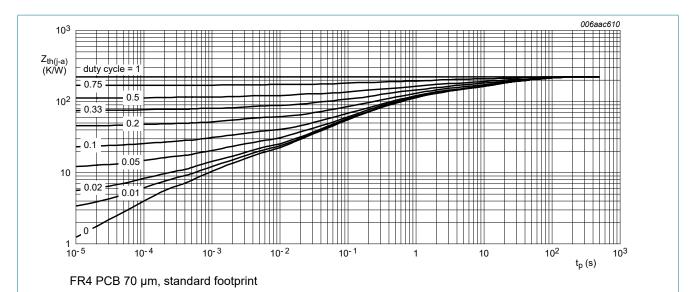


Fig. 6. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

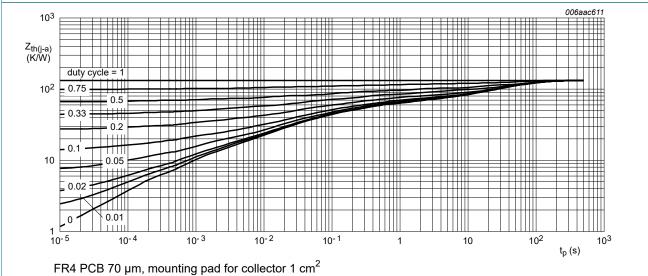


Fig. 7. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

8 / 17

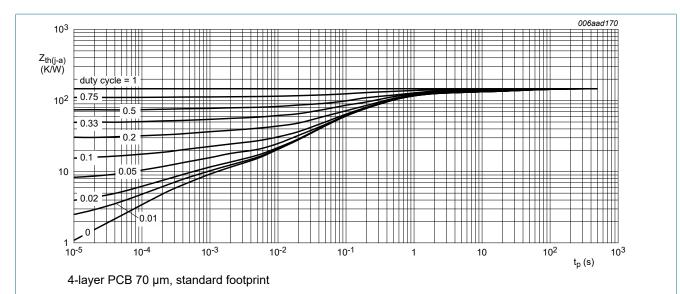


Fig. 8. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

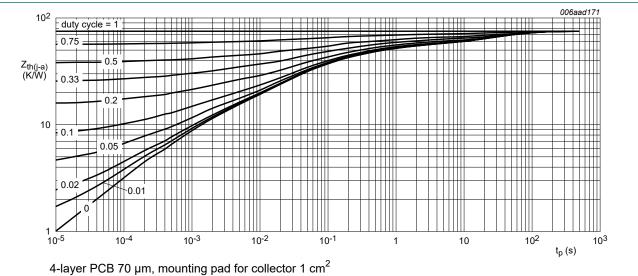


Fig. 9. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

PBSS5130PAP

# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -24 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	250	350	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	170	250	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	120	175	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-85	-140	mV
		$I_C$ = -1 A; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-175	-280	mV
	$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-160	-250	mV	
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -1 A; $I_B$ = -0.1 A; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	250	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	-	-1	V
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; T <sub>amb</sub> = 25 °C	-	-	-1	V
		$I_C$ = -1 A; $I_B$ = -100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = -10 V; I <sub>C</sub> = -0.5 A; I <sub>Bon</sub> = -25 mA;	-	15	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = 25 mA; T <sub>amb</sub> = 25 °C	-	35	-	ns
t <sub>on</sub>	turn-on time		-	50	-	ns
t <sub>s</sub>	storage time		-	105	-	ns
t <sub>f</sub>	fall time		-	35	-	ns
t <sub>off</sub>	turn-off time		-	140	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	65	125	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	13	17	pF

### 30 V, 1 A PNP/PNP low VCEsat transistor

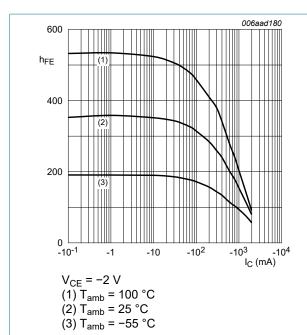


Fig. 10. DC current gain as a function of collector current; typical values

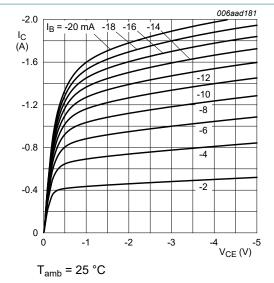


Fig. 11. Collector current as a function of collectoremitter voltage; typical values

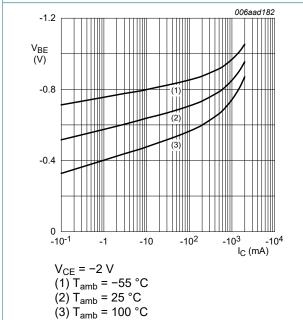
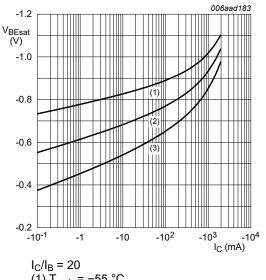


Fig. 12. Base-emitter voltage as a function of collector current; typical values



(1)  $T_{amb} = -55$  °C (2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 13. Base-emitter saturation voltage as a function of collector current; typical values

30 September 2025

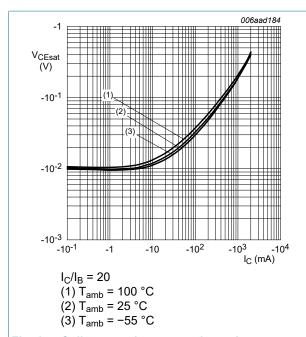


Fig. 14. Collector-emitter saturation voltage as a function of collector current; typical values

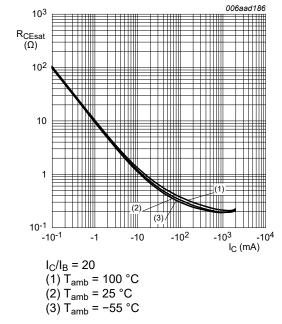


Fig. 16. Collector-emitter saturation resistance as a function of collector current; typical values

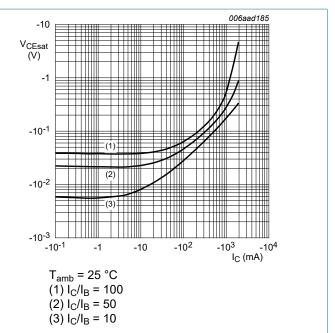


Fig. 15. Collector-emitter saturation voltage as a function of collector current; typical values

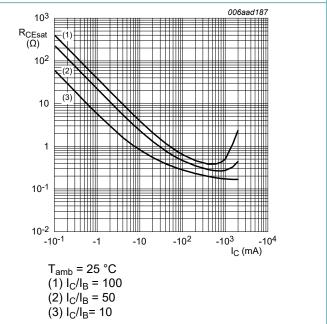
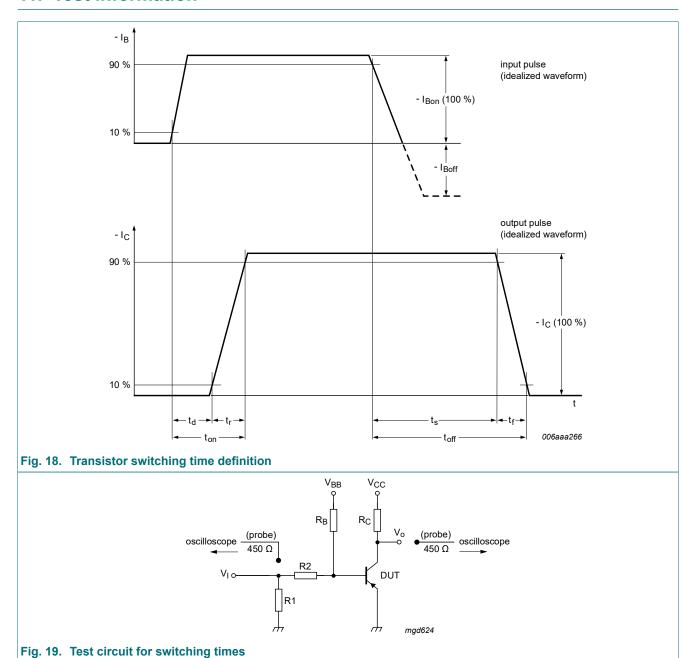


Fig. 17. Collector-emitter saturation resistance as a function of collector current; typical values

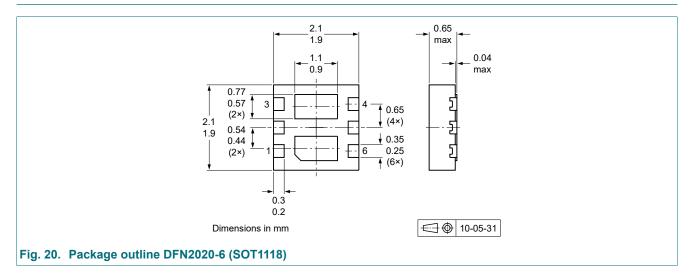
### 30 V, 1 A PNP/PNP low VCEsat transistor

## 11. Test information

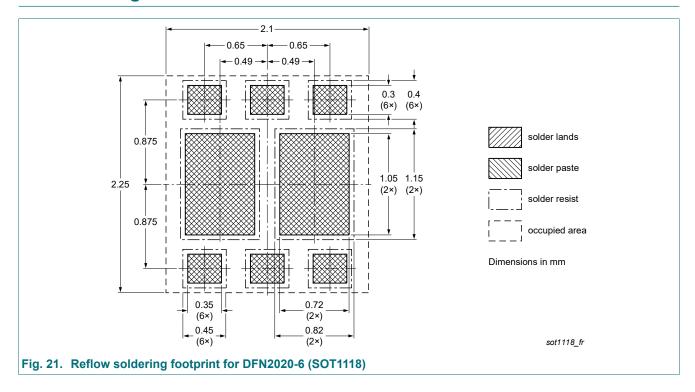


30 V, 1 A PNP/PNP low VCEsat transistor

# 12. Package outline



## 13. Soldering



30 September 2025

## 30 V, 1 A PNP/PNP low VCEsat transistor

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBSS5130PAP v.2	20250930	Product data sheet	-	PBSS5130PAP v.1				
Modifications:	( )	Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).						
PBSS5130PAP v.1	20050421	Product data sheet	-	-				

15 / 17

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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## 30 V, 1 A PNP/PNP low VCEsat transistor

## **Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	. 3
9.	Thermal characteristics	. 5
10.	Characteristics	10
11.	Test information	13
12.	Package outline	14
13.	Soldering	14
14.	Revision history	15
	Legal information	

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